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Corrigendum

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Y.F. Mei^a, Ricky K.Y. Fu^a, G.G. Siu^a, Paul K. Chu^{a,*}, Z.M. Li^b, C.L. Yang^b, W.K. Ge^b, Z.K. Tang^b, W.Y. Cheung^c, S.P. Wong^c

^aDepartment of Physics and Materials Science, City University of Hong Kong, Tat Chee Avenue, Kowloon, Hong Kong, China ^bDepartment of Physics, Hong Kong University of Science & Technology, Clear Water Bay, Kowloon, Hong Kong, China ^cDepartment of Electronic Engineering, Chinese University of Hong Kong, Shatin, Hong Kong, China

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The authors regret that when this article was published, Paul K. Chu was affiliated to the incorrect institution. Paul K. Chu is affiliated to Department of Physics and Materials Science, City University of Hong Kong, Tat Chee Avenue, Kowloon, Hong Kong, China.

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E-mail address: paul.chu@cityu.edu.hk (P.K. Chu).

^{*}Corresponding author. Tel.: +852 278 87 724; fax: +852 2788 9549, +852 2788 7830.